

# NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

## Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.50\text{ V}$  at  $I_F = 5\text{ A}$

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

### Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

### Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

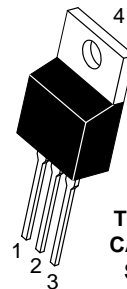
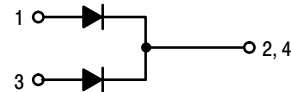


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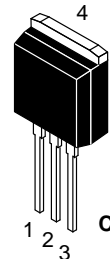
[www.onsemi.com](http://www.onsemi.com)

VERY LOW FORWARD VOLT-  
AGE, LOW LEAKAGE SCHOT-  
TKY BARRIER  
RECTIFIERS 30 AMPERES,  
120 VOLTS

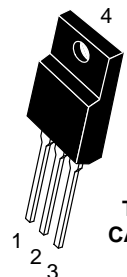
### PIN CONNECTIONS



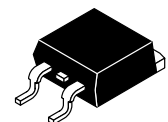
TO-220AB  
CASE 221A  
STYLE 6



I2PAK  
CASE 418D  
STYLE 3



TO-220FP  
CASE 221AH



D2PAK  
CASE 418B

### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	120	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 125^\circ\text{C}$ )	$I_{F(AV)}$ Per device Per diode	30 15	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 130^\circ\text{C}$ )	$I_{FRM}$ Per device Per diode	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	150	A
Operating Junction Temperature	$T_J$	-40 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Rating	Symbol	NTST30120CTG NTSB30120CT-1G	NTSB30120CTG	NTSJ30120CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.5 70	1.14 46.6	4.05 105	$^\circ\text{C/W}$ $^\circ\text{C/W}$

## ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

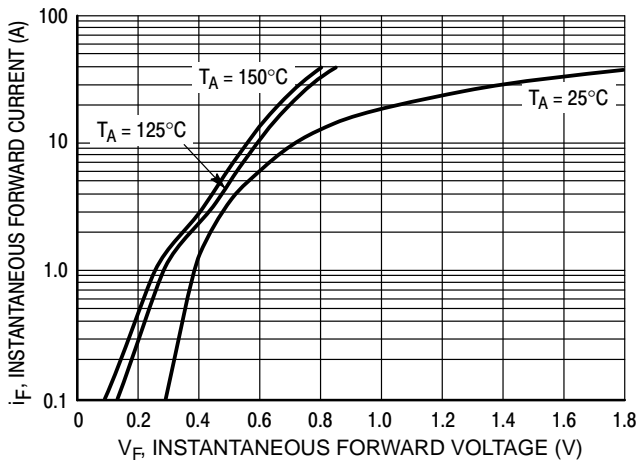
Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) ( $I_F = 5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 7.5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 15\text{ A}$ , $T_J = 25^\circ\text{C}$ )  ( $I_F = 5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 7.5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 15\text{ A}$ , $T_J = 125^\circ\text{C}$ )	$V_F$	0.56 0.71 0.90  0.50 0.60 0.68	— — 1.08  — — 0.76	V
Maximum Instantaneous Reverse Current (Note 1) ( $V_R = 90\text{ V}$ , $T_J = 25^\circ\text{C}$ ) ( $V_R = 90\text{ V}$ , $T_J = 125^\circ\text{C}$ )  (Rated dc Voltage, $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$I_R$	16 11  — 25	— —  800 100	$\mu\text{A}$ mA  $\mu\text{A}$ mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

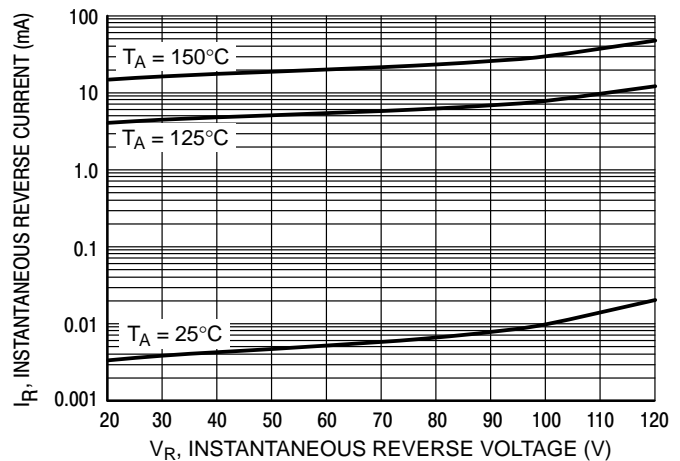
1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG,  
NTSB30120CTT4G**

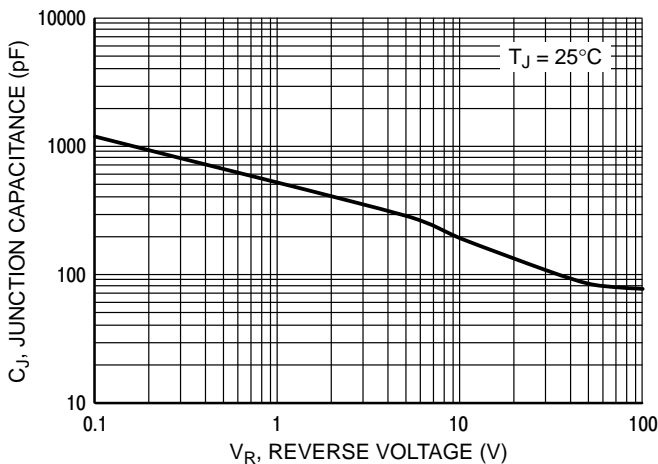
**TYPICAL CHARACTERISTICS**



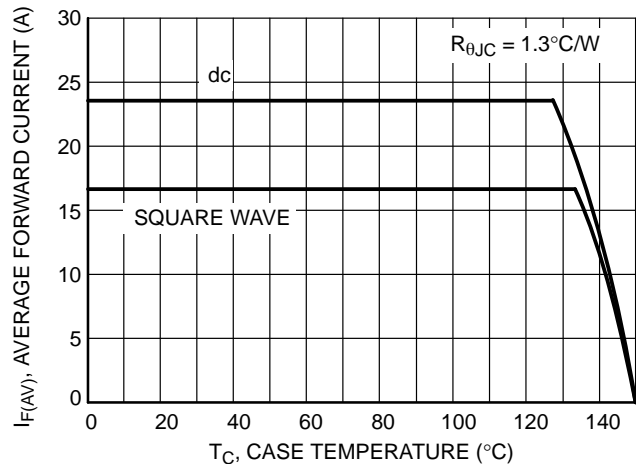
**Figure 1. Typical Instantaneous Forward Characteristics**



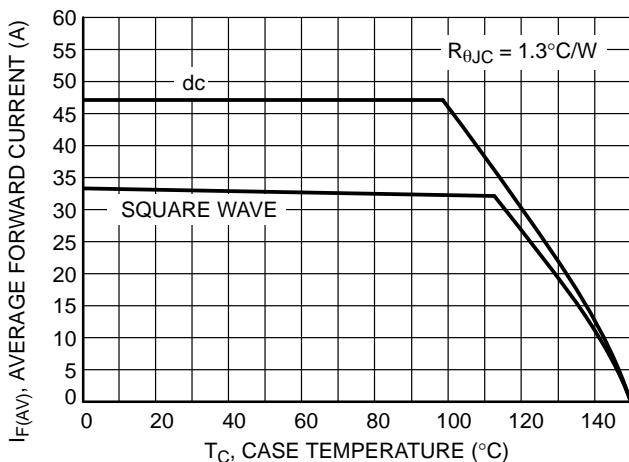
**Figure 2. Typical Reverse Current Characteristics**



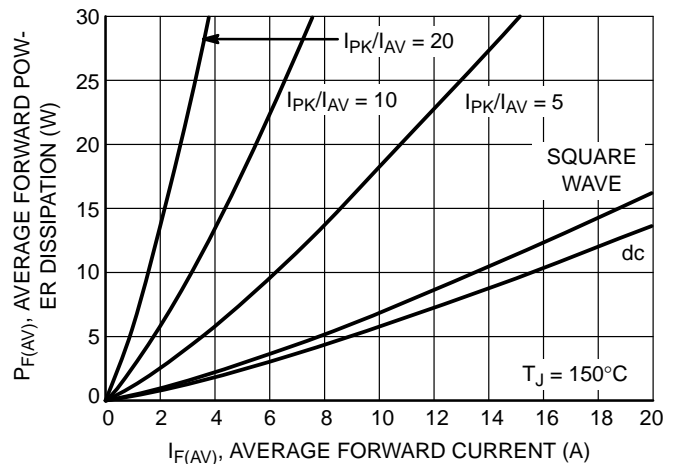
**Figure 3. Typical Junction Capacitance**



**Figure 4. Current Derating per Leg**



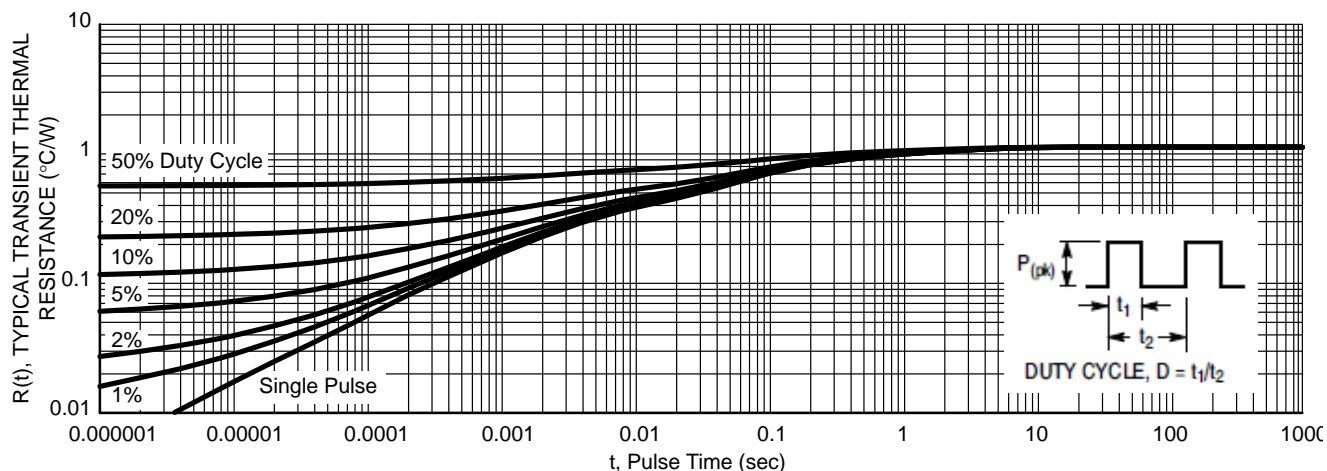
**Figure 5. Current Derating**



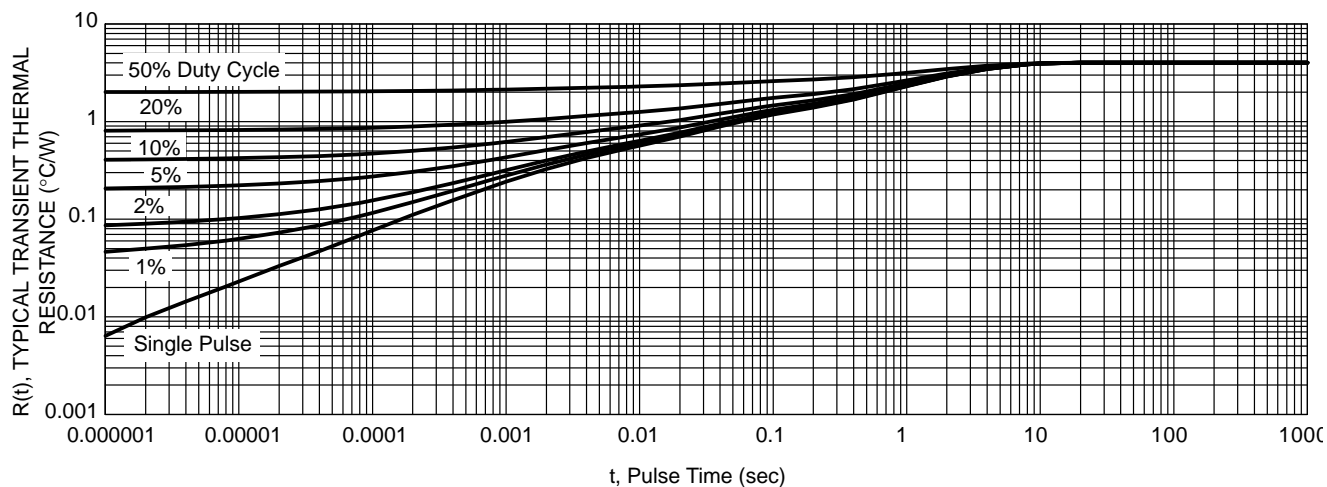
**Figure 6. Forward Power Dissipation**

**NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG,  
NTSB30120CTT4G**

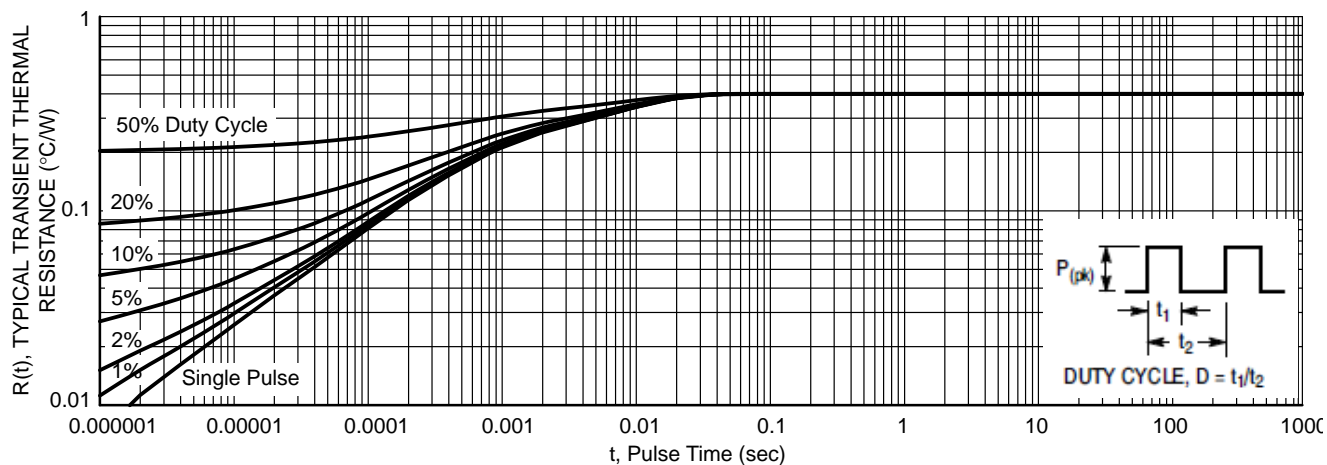
**TYPICAL CHARACTERISTICS**



**Figure 7. Typical Transient Thermal Response for NTST30120CT and NTSB30120CT-1G**



**Figure 8. Typical Transient Thermal Response for NTSJ30120CTG**



**Figure 9. Typical Transient Thermal Response for NTSB30120CTG**

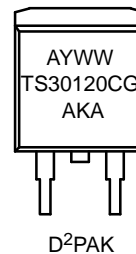
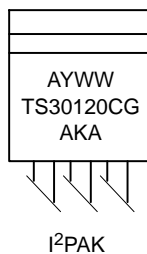
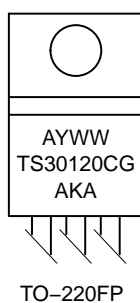
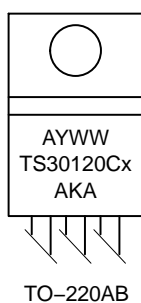
# NTST30120CT, NTSJ30120CTG, NTSB30120CT-1G, NTSB30120CTG, NTSB30120CTT4G

## ORDERING INFORMATION

Device	Package	Shipping†
NTST30120CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTSJ30120CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB30120CT-1G	I <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB30120CTG	D <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB30120CTT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

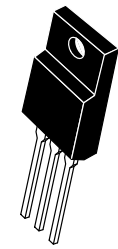
## MARKING DIAGRAMS



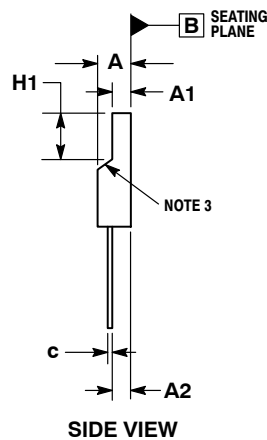
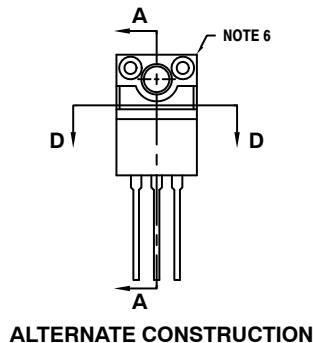
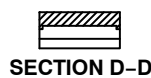
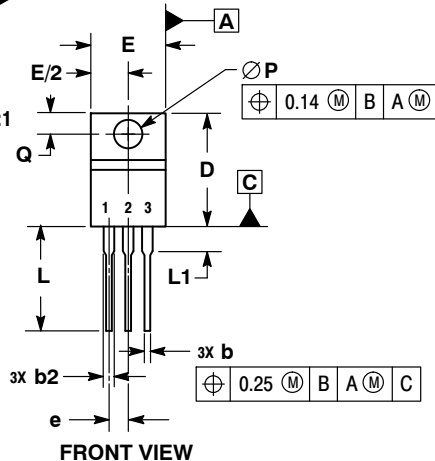
A = Assembly Location  
 Y = Year  
 WW = Work Week  
 AKA = Polarity Designator  
 x = G or H  
 G = Pb-Free Package  
 H = Halide-Free Package

### TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE F

DATE 30 SEP 2014



SCALE 1:1

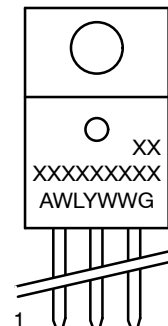


#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOPE DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

#### GENERIC MARKING DIAGRAM\*



A = Assembly Location  
WL = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE

STYLE 2:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

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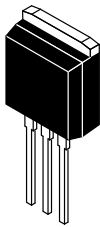
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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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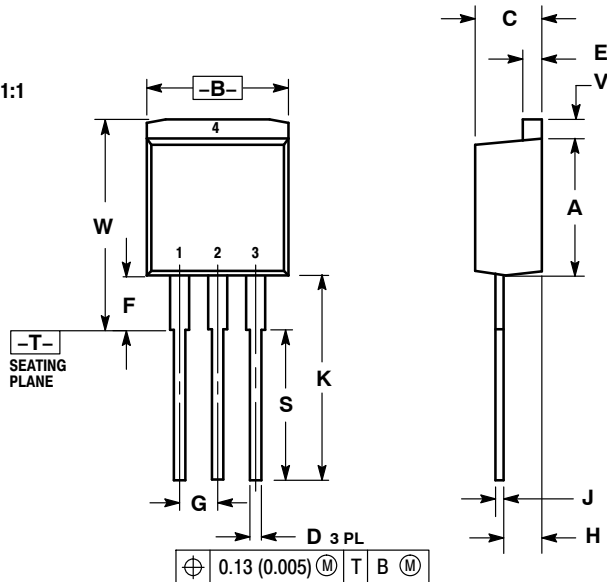
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SCALE 1:1

I<sup>2</sup>PAK (TO-262)  
CASE 418D-01  
ISSUE D

DATE 16 OCT 2007



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.380	8.51	9.65
B	0.380	0.406	9.65	10.31
C	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
E	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
H	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

### STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

### STYLE 2:

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

### STYLE 3:

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

### STYLE 4:

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

DOCUMENT NUMBER: 98ASB16716C

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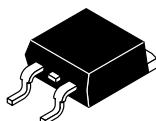
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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

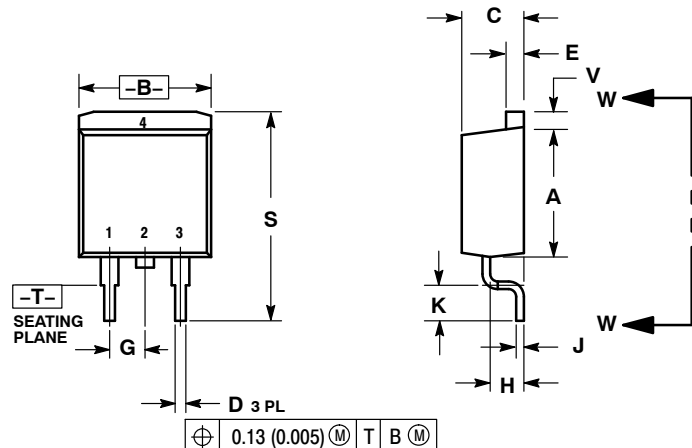
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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

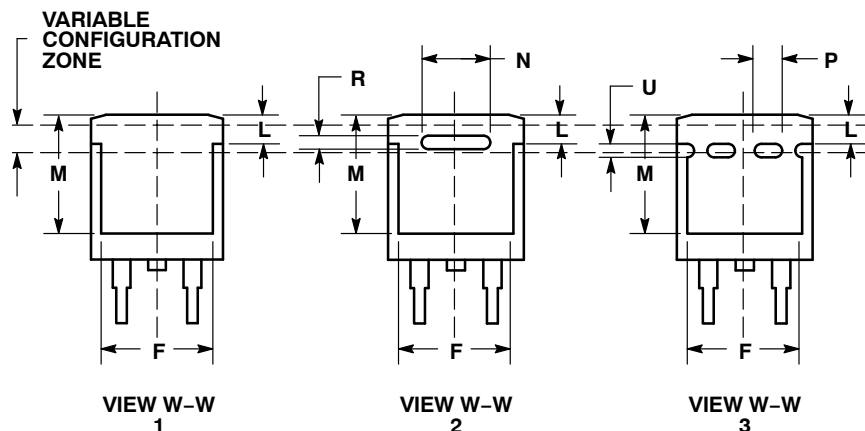
DATE 17 FEB 2015

SCALE 1:1



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



- |              |             |              |              |                |                   |
|--------------|-------------|--------------|--------------|----------------|-------------------|
| STYLE 1:     | STYLE 2:    | STYLE 3:     | STYLE 4:     | STYLE 5:       | STYLE 6:          |
| PIN 1. BASE  | PIN 1. GATE | PIN 1. ANODE | PIN 1. GATE  | PIN 1. CATHODE | PIN 1. NO CONNECT |
| 2. COLLECTOR | 2. DRAIN    | 2. CATHODE   | 2. COLLECTOR | 2. ANODE       | 2. CATHODE        |
| 3. EMITTER   | 3. SOURCE   | 3. ANODE     | 3. EMITTER   | 3. CATHODE     | 3. ANODE          |
| 4. COLLECTOR | 4. DRAIN    | 4. CATHODE   | 4. COLLECTOR | 4. ANODE       | 4. CATHODE        |

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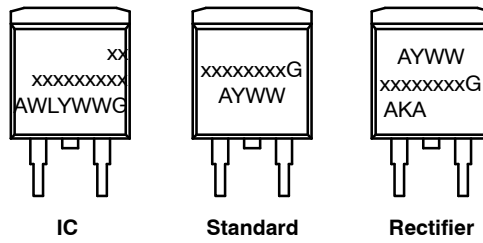
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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

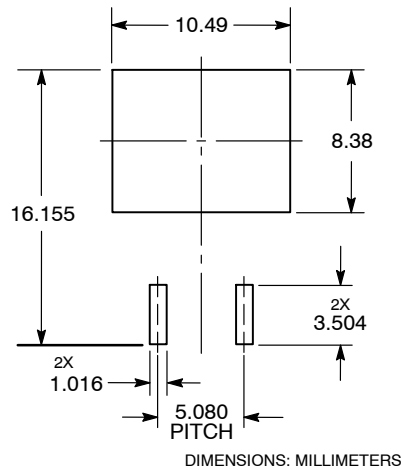
**GENERIC  
MARKING DIAGRAM\***



xx        = Specific Device Code  
A        = Assembly Location  
WL      = Wafer Lot  
Y        = Year  
WW      = Work Week  
G        = Pb-Free Package  
AKA     = Polarity Indicator


\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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